



Second generation Front-end chip for H-Cal SiPM readout : SPIROC

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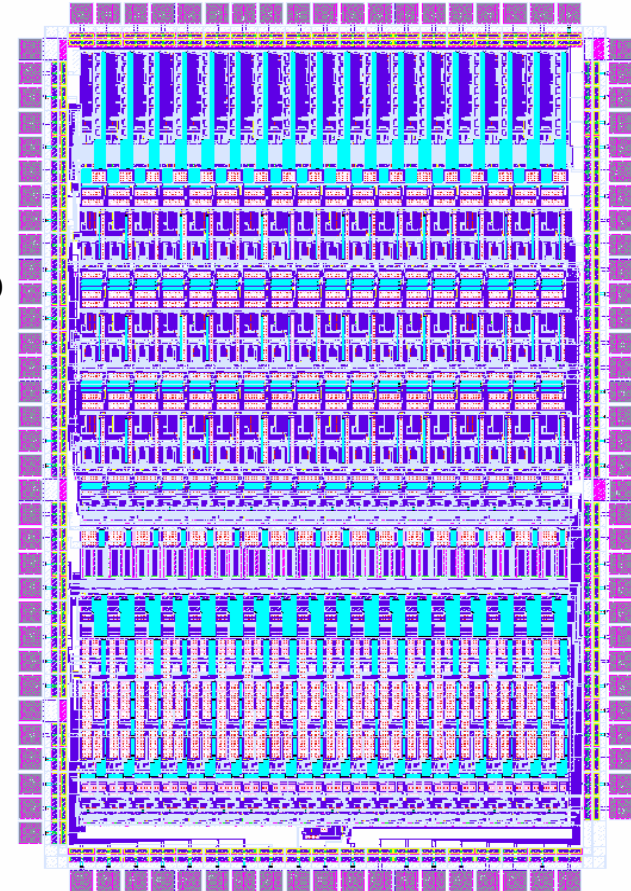
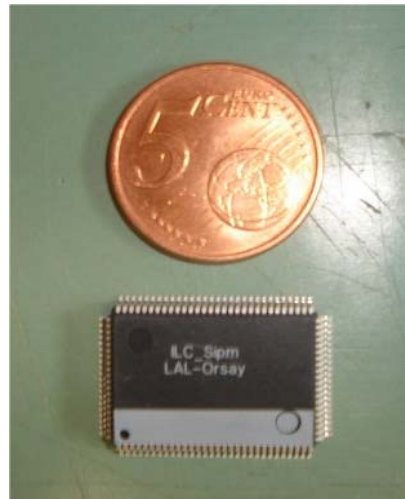
DESY Hamburg – le 13 février 2007

First generation chip for SiPM : short reminder

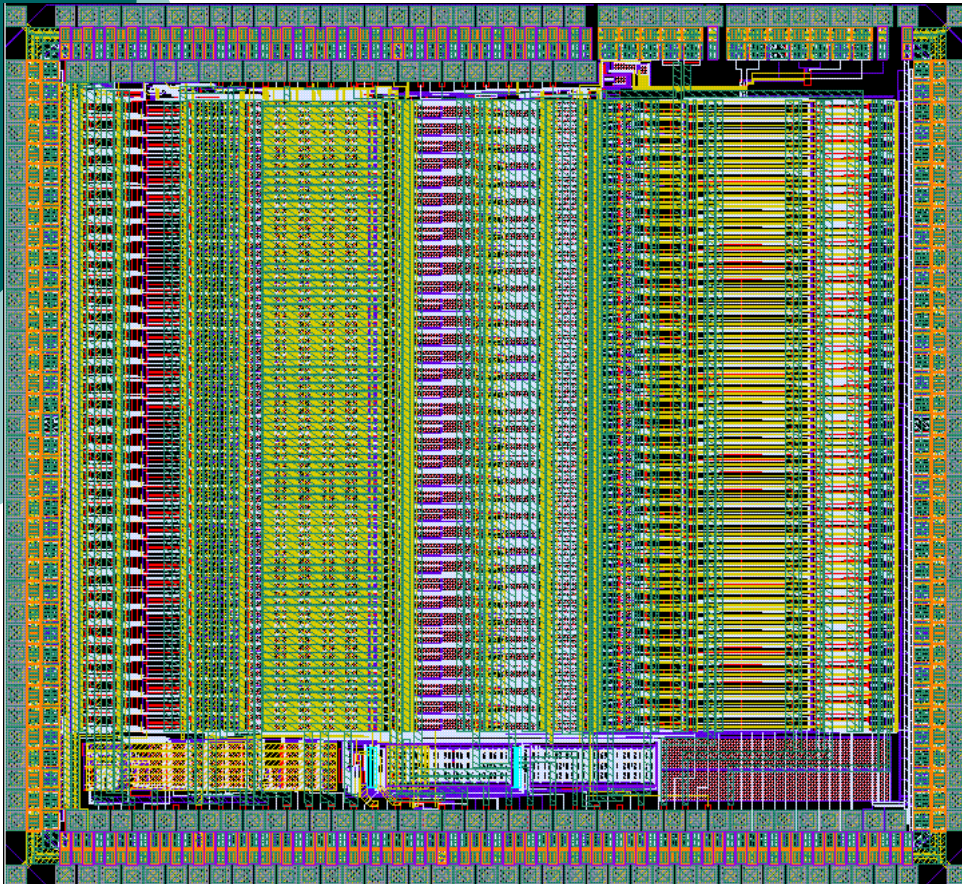
18-channel 8-bit DAC (0-5V)

18-channel front-end readout :

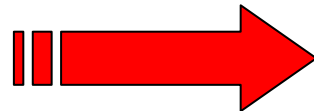
- Variable gain charge preamplifier (0.67 to 10 V/pC)
 - Variable time constant CRRC² shaper (12 to 180 ns)
 - Track and hold → 1 multiplexed output
 - Power consumption : ~**200mW** (supply : **0-5V**)
-
- Technology : **AMS 0.8 μm CMOS**
 - Chip area : ~ **10mm²**
 - Package : **QFP-100**



Second generation chip for SiPM : SPIROC



Skiroc layout :
~20mm²



- A-HCAL read out
- Silicon PM detector
- 36 channels
- Compatible with new DAQ
- Many SKIROC, HARDROC, and MAROC features re-used

Technology : AMS 0.35 μm SiGe

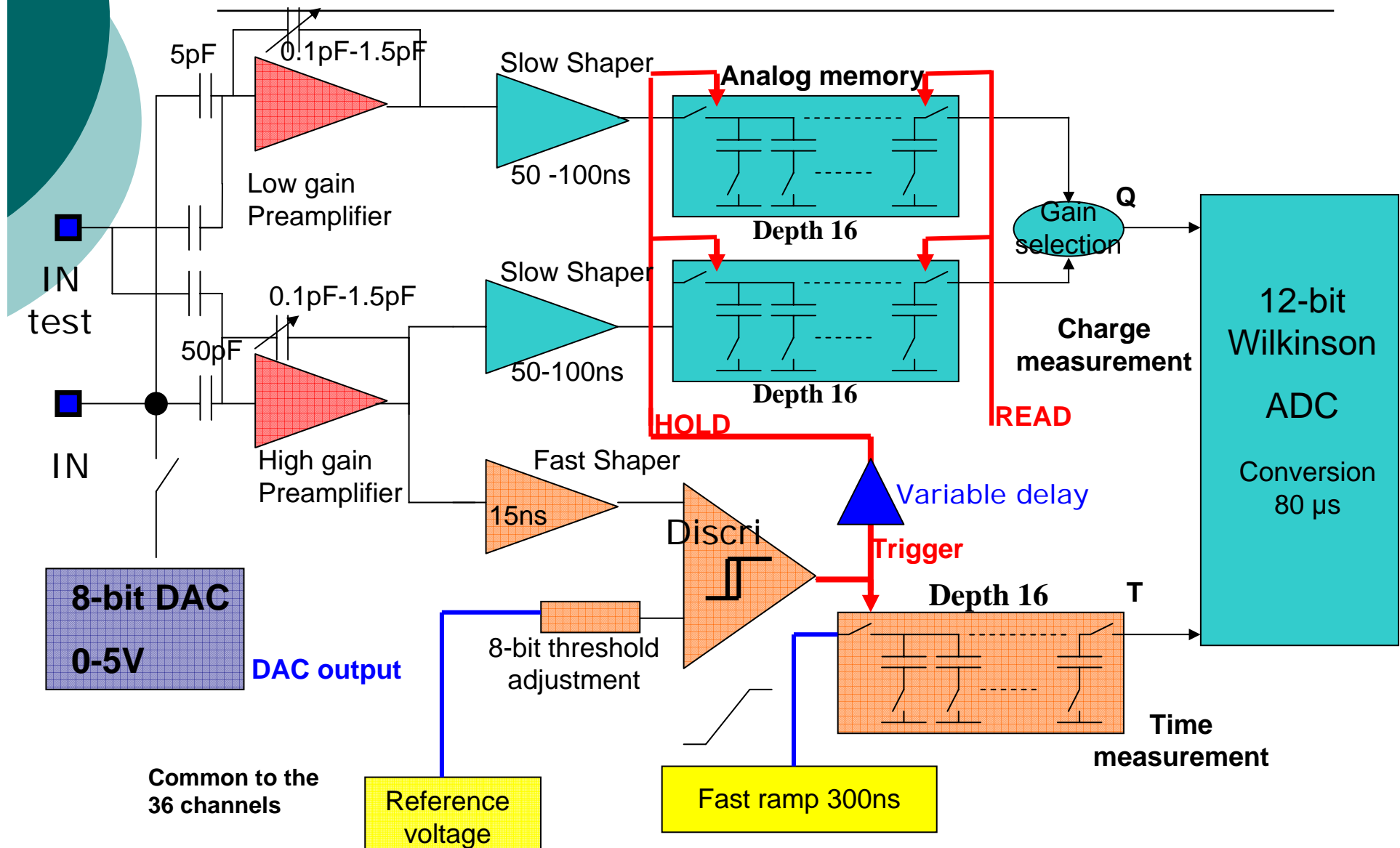
SPIROC submission expected on
11th june



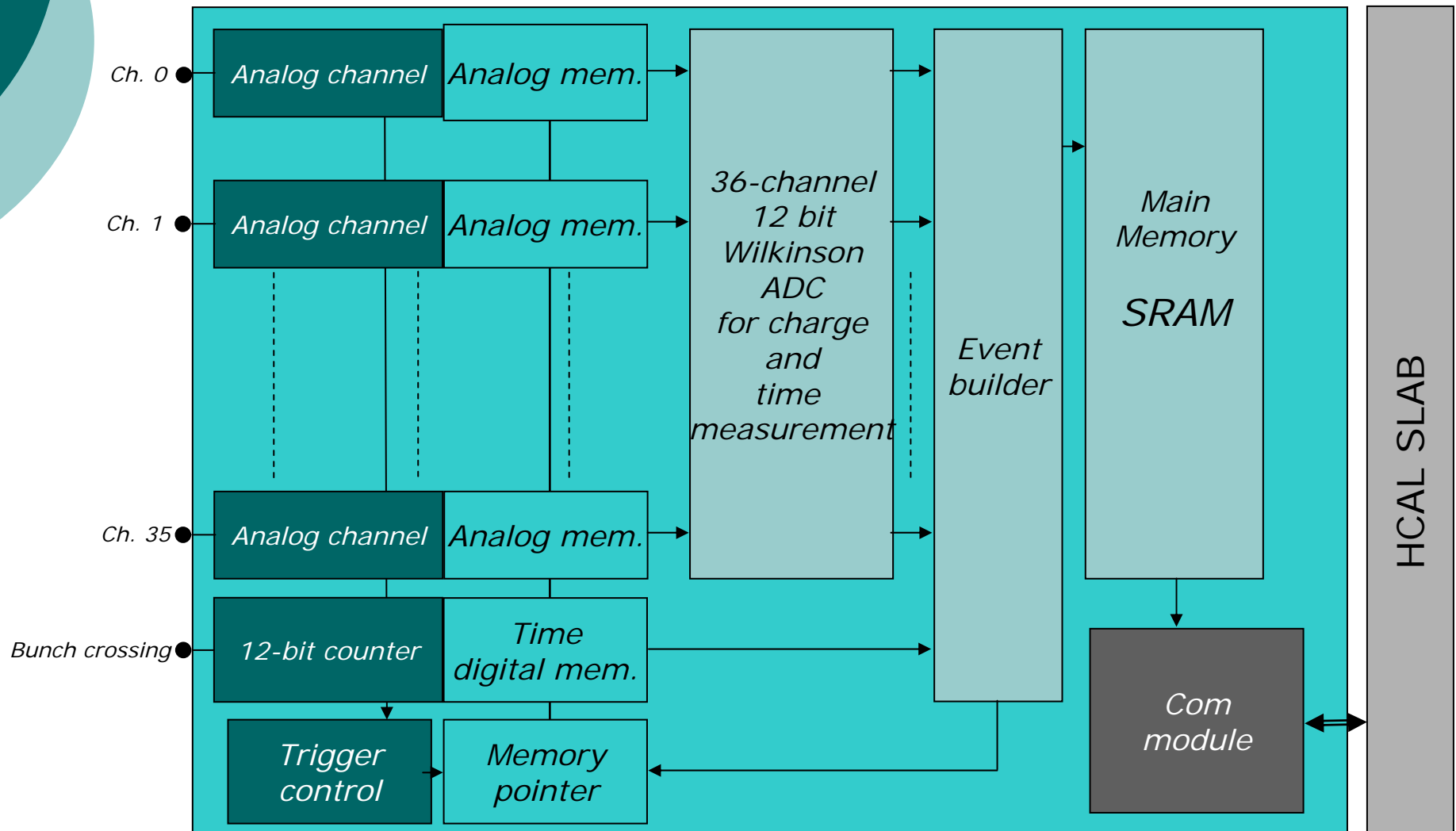
SPIROC main features

- 36-channel readout chip
- Internal input 8-bit DAC (0-5V) for SiPM gain adjustment
- Energy measurement :
 - 2 gains / 12 bit ADC 1 pe \rightarrow 2000 pe
 - Variable shaping time from 50ns to 100ns
 - pe/noise ratio : 11
- Time measurement :
 - 1 TDC (12 bits) step \sim 100 ps
 - pe/noise ratio on trigger channel : 24
 - Fast shaper : \sim 15ns
 - Auto-Trigger on $\frac{1}{2}$ pe
- Analog memory for time and charge measurement : depth 16
- Power pulsing integrated
- Low consumption : \sim 25 μ W per channel (in power pulsing mode)
- Calibration injection capacitance
- Embedded bandgap for voltage references
- Embedded DAC for trigger threshold
- Compatible with physic prototype DAQ
 - Serial analogue output
 - External "force trigger"
- Probe bus for debug
- 12-bit Bunch Crossing ID
- SRAM with data formatting 2 x 2kbytes = 4kbytes
- Output & control with daisy-chain

SPIROC: One channel schematic

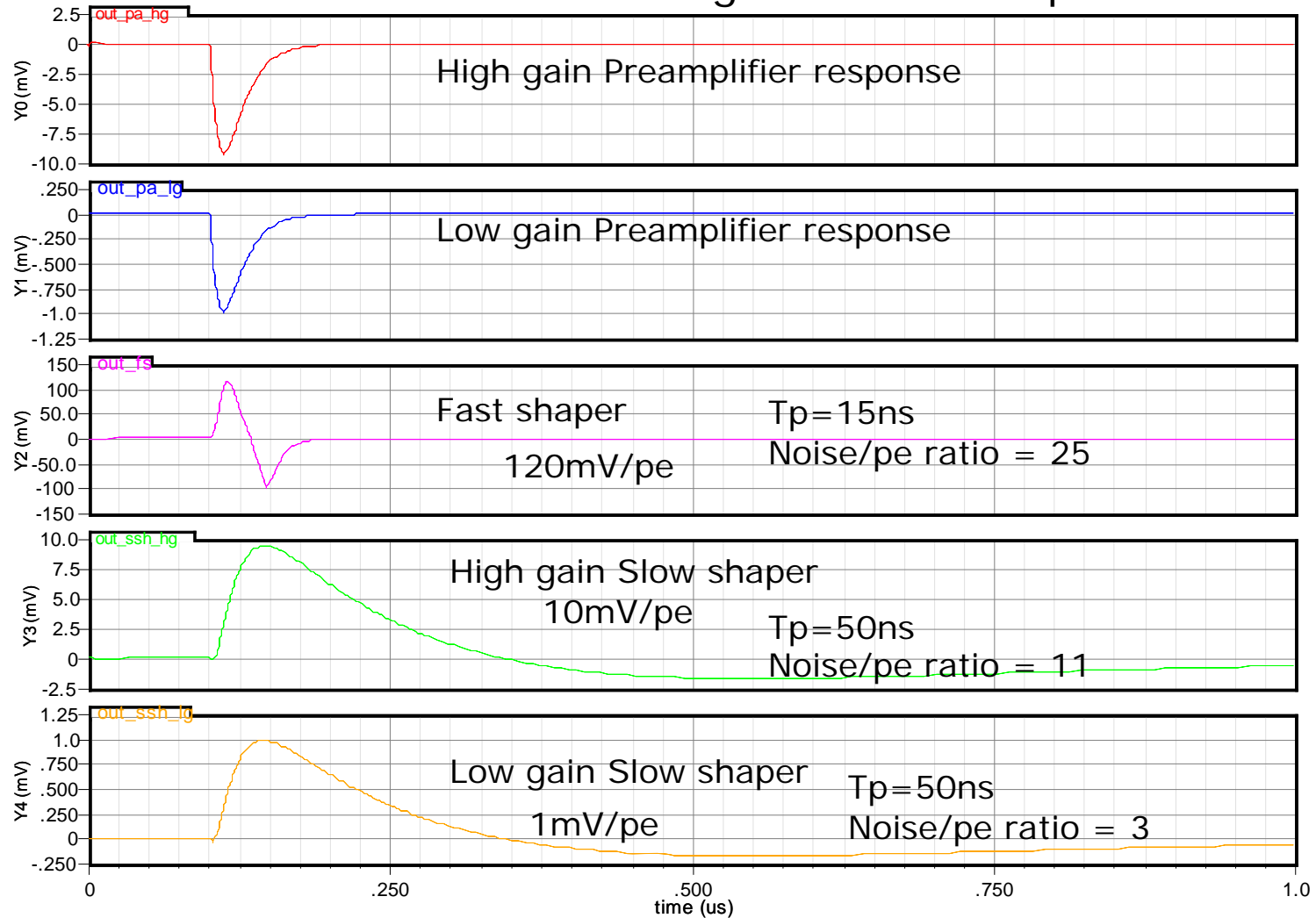


Block scheme of SPIROC

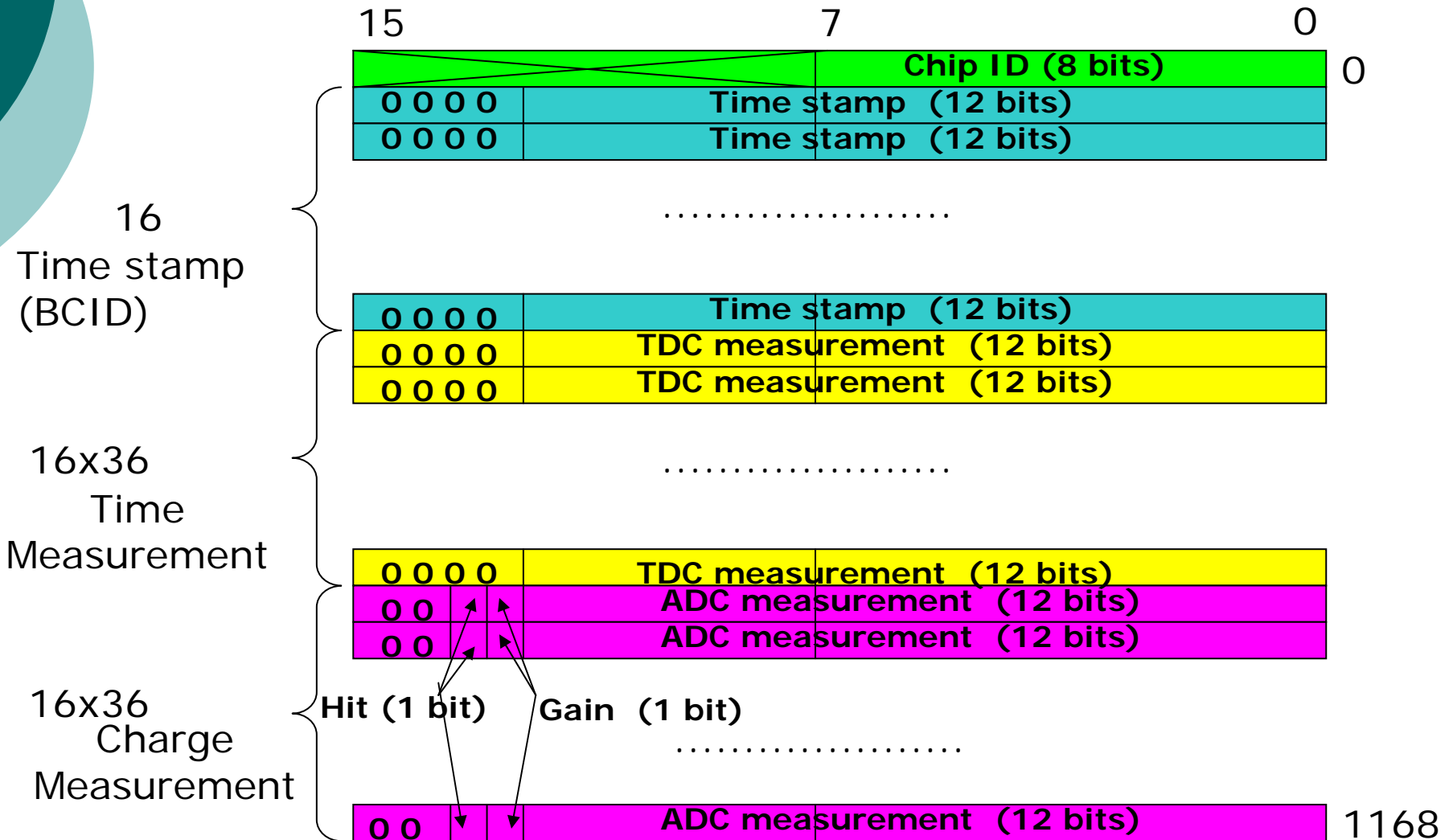


SPIROC : Photoelectron response simulation

Expressions
Simulation obtained with SiPM gain = 10^6 - 1 pe = 160 fC

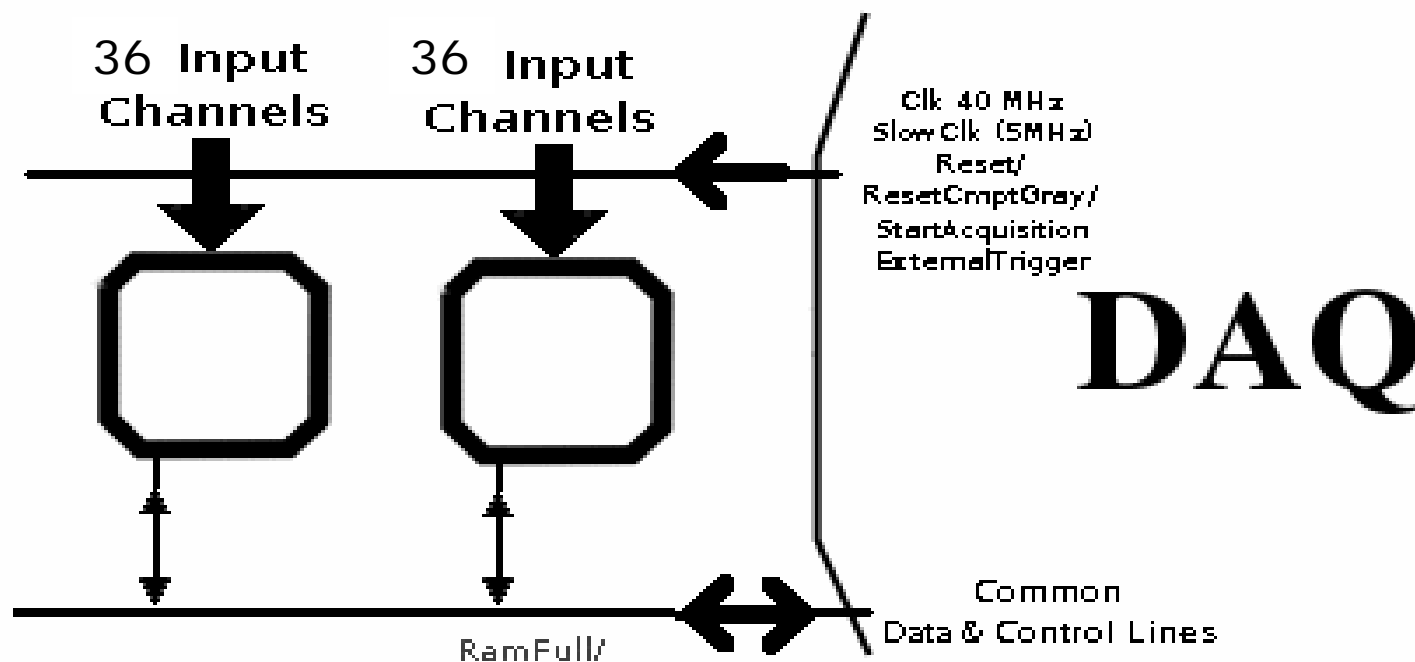


SPIROC : RAM Mapping



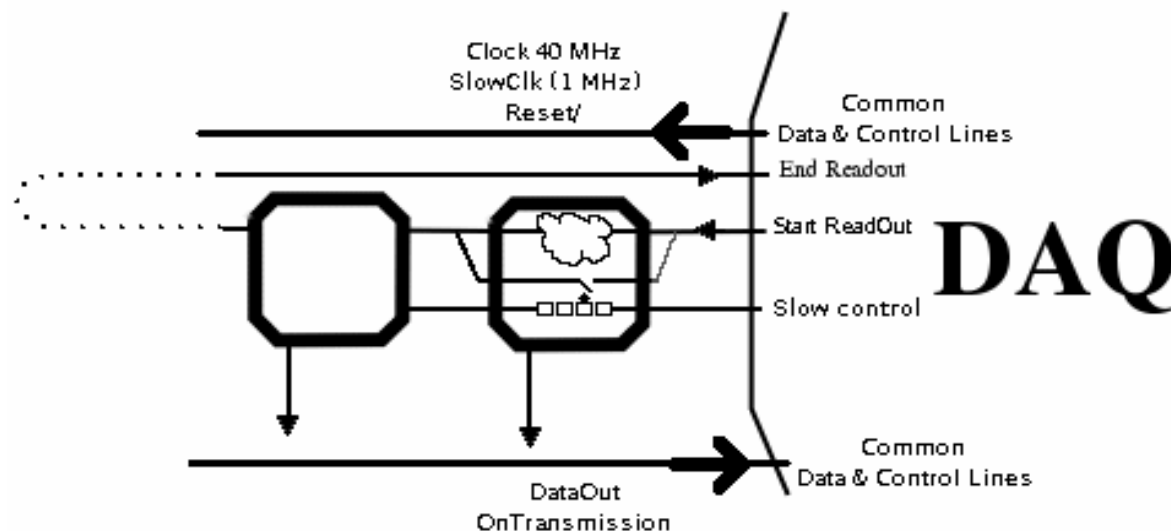
SPIROC : Acquisition mode

- Store up to 16 events in RAM
- Stop acquisition when ram_full signal asserted
 - Common collector bus for ram_full signal

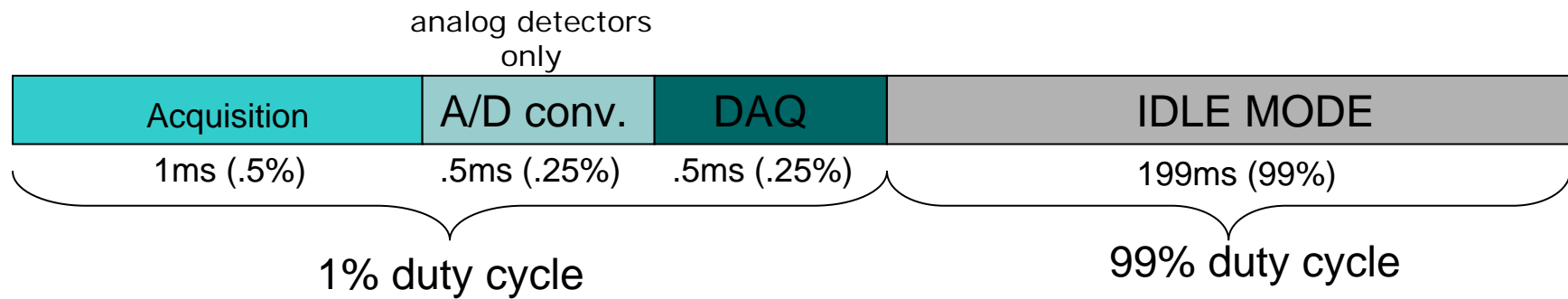
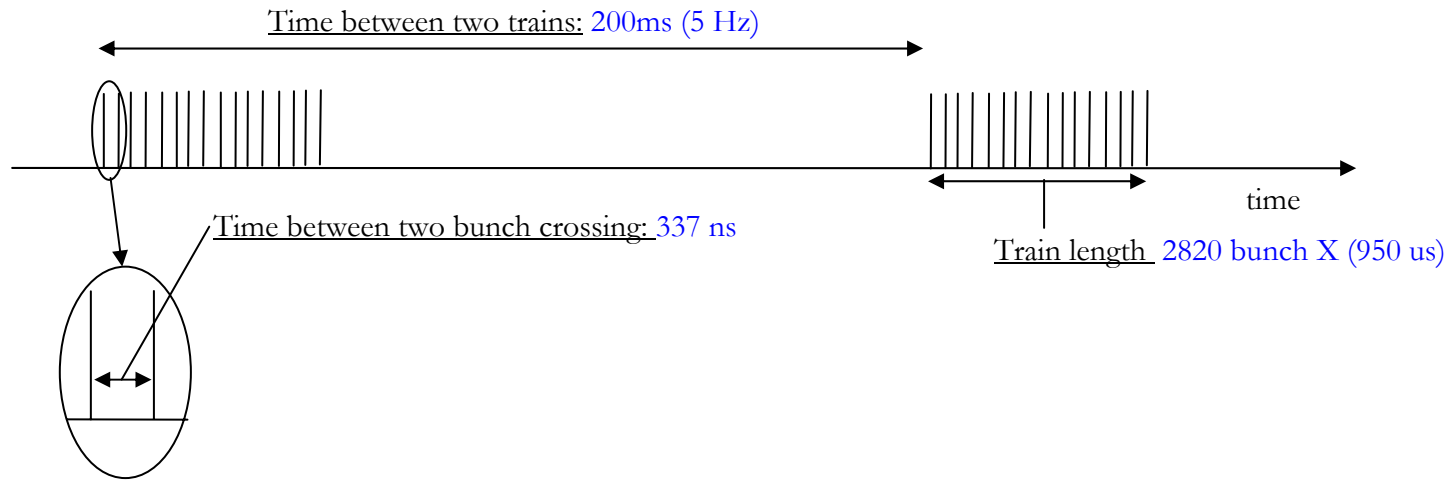


SPIROC : Readout mode

- Based on daisy chain mechanism initiated by DAQ
 - Possibility to bypass a chip by slow control
- One data line activated by each chip sequentially
 - Readout rate few MHz to minimize power dissipation
 - With 500 pF bus capacitance, power dissipation is $\sim 10\mu\text{W}/\text{chip}$
 - $i = C dV/dt = 1 \text{ mA} \Rightarrow 1 \text{ mW}$ for up to 100 chips on bus
 - Readout time max (ram full) $20\text{kbits} \times 1 \mu\text{s} = 20 \text{ ms}/\text{chip}$



Time considerations





Schedule

- First Prototype submission : 11th June 2007
- Expected delivery : September 2007
- SPIROC Characterization : End of Year



Conclusion

- SPIROC designed for SiPM A-HCAL : second generation ASICs
- Many SKIROC, HARDROC, and MAROC features re-used for SPIROC : power pulsing, bandgap, daisy chain mechanism, etc.
- New features embedded : Time measurement, low consumption input DAC, etc.
- Compatible with new DAQ
- Complexity is increasing
- Submission in June 2007 and first prototype expected in September 2007